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204	Raised Source/Drain on 50nm CMOS Circuits : Propagation Delay and Dynamic Power Optimizations	CMOS and Memory Devices
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96	Lithography Independent Fabrication of Nano-MOS-Transistors with W = 25 nm and L = 25 nm	ITRS Roadblocks, Models and Process Steps
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105	Stability of High-k Thin Films in Moisture Ambience - The Effect of Dissolution Gas from Acryl Apparatus -	ITRS Roadblocks, Models and Process Steps
106	Electrical Characteristics Improvement of Dy2O3 Thin Films by In-situ Vacuum Anneal	ITRS Roadblocks, Models and Process Steps
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195	Gate oxide process impact on RNCE for advanced CMOS transistors	ITRS Roadblocks, Models and Process Steps
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224	Determination of beryllium and self-interstitial parameters for modeling of Be activation implanted in InGaAs	ITRS Roadblocks, Models and Process Steps

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229	Investigation of HfO2 dielectric stacks deposited by ALD with a mercury probe	ITRS Roadblocks, Models and Process Steps
238	Thermal Nitridation of Chemical Dielectrics as an Easy Approach to Ultra-thin Gate Oxide Processing	ITRS Roadblocks, Models and Process Steps
239	Direct-Current Performance Improvements of Al0.45Ga0.55As/GaAs Digital Graded Superlattice-Emitter Heterojunction Bipolar Transistors by Wet-Oxidation	ITRS Roadblocks, Models and Process Steps
249	ZrO2 gate dielectrics prepared by e-beam deposition of Zr and YSZ films and post annealing processes	ITRS Roadblocks, Models and Process Steps
250	Optimization of Single Halo p-MOSFET Implant Parameters for Improved Analog Performance and Reliability	ITRS Roadblocks, Models and Process Steps
261	A New Compact Horizontal Current Bipolar Transistor (HCBT) Fabricated in (110) Wafers	ITRS Roadblocks, Models and Process Steps
269	RPN Oxynitride Gate Dielectrics for 90 nm Low Power CMOS Applications	ITRS Roadblocks, Models and Process Steps
2	Noise Analysis for a SiGe HBT by Hydrodynamic Device Simulation	Modeling and Characterization
4	Compact LDD/FD SOI CMOS Device Model Considering Energy Transport and Self Heating for SPICE Circuit Simulation	Modeling and Characterization
11	Evaluation of Interface Trap Density in a SiGe/Si Heterostructure Using a Charge Pumping Technique and Correlation between the Trap Density and Low Frequency Noise in SiGe-Channel pMOSFETs	Modeling and Characterization
12	Compact Breakdown Model for PD SOI NMOS Devices Considering BJT/MOS Impact Ionization for SPICE Circuit Simulation	Modeling and Characterization
13	A New Physical Modeling of Parasitic Capacitances of Deep-Submicron LDD MOSFETs	Modeling and Characterization
14	Dissipative transport in quantum wires	Modeling and Characterization
15	Influence of the Extrinsic Base on the Base Current Kink in SiGe BJTs	Modeling and Characterization
17	Static and RF behaviour of short-gate Fully-Depleted Silicon-on-Insulator MOSFETs: numerical and experimental analysis	Modeling and Characterization
18	Small Signal Characterization of Thin Film Single Halo SOI MOSFET For Mixed Mode Analog and Digital Applications	Modeling and Characterization
22	Comments on Existing 1/f Noise Models:Spice, HSPICE and BSIM3v3 for MOSFETs in Circuit Simulators	Modeling and Characterization
27	Nano crystal memory devices characterization using the charge pumping technique	Modeling and Characterization
28	Properties of Vacancies in Silicon Determined from LaserAnnealing Experiments	Modeling and Characterization
29	Gate and Drain Bias Dependences of 1/f Noise Amplitude in MOSFETs in the Linear and Saturation Regions	Modeling and Characterization
33	Self-Consistent Solution of the Schrodinger and Poisson Equations for Accumulated MOS Capacitors with Ultra-thin Layers	Modeling and Characterization
34	Extraction of Si-SiO2 interface trap densities in MOSFET's with oxides down to 1.3 nm thick	Modeling and Characterization
35	Modeling of Large-Area nMOS Devices for Smart-Power Applications	Modeling and Characterization
38	Extraction method for the impact-ionization multiplication factor in silicon at large operating temperatures	Modeling and Characterization
41	Threshold Variations for Undoped Double-Gate MOSFET's	Modeling and Characterization
42	Effects of Boron and Germanium Base Profiles on SiGe and SiGe:C BJT Characteristics	Modeling and Characterization
43	Simulation and Modeling of Nanocrystalline Silicon Thin Film Transistors	Modeling and Characterization
45	SILC Measurements of Thin SiO2 at Low Voltages: High-resolution measurements and interpretation	Modeling and Characterization
47	Coupled Monte Carlo Simulation of Si and SiO2 Transport in MOS Transistors	Modeling and Characterization
48	Metal Rings as Quantum Bits	Modeling and Characterization

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55	On the origin of the 1/f1.7 noise in deep submicron partially depleted SOI transistors	Modeling and Characterization
60	Impact of Scaling Down from 0.25um to 0.18um CMOS Technology on 1/f Noise: Characterisation and Modelling	Modeling and Characterization
64	Characteristics of Polysilicon Resistors for Sub-Quarter Micron CMOS Applications	Modeling and Characterization
68	Inversion Layer Quantization Impact on the Interpretation of 1/f Noise in Deep Submicron CMOS Transistors	Modeling and Characterization
72	Microwave noise Modeling of the 0.18um Gate Length Mosfets with a 60GHz cut-off frequency	Modeling and Characterization
74	Modeling the C-V Characteristics of Heterodimensional Schottky Contacts	Modeling and Characterization
77	Implantation Dose Profiling by MOS C-V Measurements	Modeling and Characterization
79	Compact Quantum Mechanical Device Models for MOSFETs in Gigascale Integration(GSI)	Modeling and Characterization
80	Transmission Coefficient Estimation for High-K Gate Stack Evaluation	Modeling and Characterization
89	Deep Trap Modelling and Transient Measurements of a-Si:H p-i-n Diodes	Modeling and Characterization
95	A New Improved Model for LDMOS Transistors under Different Gate and Drain Bias Conditions	Modeling and Characterization
97	Investigating 50nm channel length vertical MOSFET containing a dielectric pocket, in a circuit environment	Modeling and Characterization
98	A method for extraction of power dissipating sources from interferometric thermal mapping measurements	Modeling and Characterization
102	Implementing Self-Heating Effects into a Volterra Simulator	Modeling and Characterization
104	Scaling considerations for fully-depleted SOI transistors down to the 20nm gate length regime	Modeling and Characterization
114	Accurate modeling of Quantum-Dot based Multi Tunnel Junction Memory: Optimization and process dispersions analyzes for DRAM applications	Modeling and Characterization
118	Investigation of the Thermal Noise of MOS Transistors under	Modeling and Characterization
119	Accurate Delay Metric for On-chip Resistive Interconnect	Modeling and Characterization
121	Low frequency noise in 0.12 µm Partially and Fully Depleted SOI technology	Modeling and Characterization
125	Design and simulation of an a-Si:H/GaAs heterojunction bipolar transistor	Modeling and Characterization
127	Efficient Monte Carlo Simulation of Tunnel Currents in MOS Structures	Modeling and Characterization
128	Improved Modified Local Density Approximation for the Modeling of Size Quantization in pMOSFETs	Modeling and Characterization
132	Quasi-analytical modelling of drain current and conductance of Single Electron Transistors with MIB	Modeling and Characterization
135	Coulomb Blockade in Thin SOI Nanodevices	Modeling and Characterization
136	Mixing Sources of Intrinsic Parameter Fluctuations in the Simulation of Sub-100nm MOSFETs	Modeling and Characterization
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273	Scaling of MOSFET Transconductance with Gate Oxide Thickness and Effect of Remote Charge Scattering	Modeling and Characterization
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212	Array-Based Electrical Detector of Integrated DNA Identification System for Genetic Chip Applications	Sensors and Biosensors
220	Bulk Wafer Defects Observable in Vision Chips	Sensors and Biosensors
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254	A CMOS Compatible Single-Photon Avalanche Diode	Sensors and Biosensors
260	A Biosensor for Direct Detection of DNA Sequences Based on Capacitance Measurements	Sensors and Biosensors
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